

Numerical investigation of dislocation climb under stress and irradiation

Daphné da Fonseca, Fabien Onimus, Frédéric Mompiou, Mihai Cosmin Marinica, Edouard de Sonis, Emmanuel Clouet, Thomas Jourdan

▶ To cite this version:

Daphné da Fonseca, Fabien Onimus, Frédéric Mompiou, Mihai Cosmin Marinica, Edouard de Sonis, et al.. Numerical investigation of dislocation climb under stress and irradiation. Acta Materialia, 2022, 242, pp.118431. 10.1016/j.actamat.2022.118431. cea-03884976

HAL Id: cea-03884976 https://cea.hal.science/cea-03884976

Submitted on 5 Dec 2022

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers. L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.



Distributed under a Creative Commons Attribution 4.0 International License

Numerical investigation of dislocation climb under stress and irradiation

D. Da Fonseca^{a,d}, F. Onimus^b, F. Mompiou^{c,d}, M.-C. Marinica^a, E. de Sonis^a, E. Clouet^a, T. Jourdan^{a,*}

 ^a Université Paris-Saclay, CEA, Service de Recherches de Métallurgie Physique, 91191, Gif-sur-Yvette, France
 ^b Université Paris-Saclay, CEA, Service de Recherches Métallurgiques Appliquées, 91191, Gif-sur-Yvette, France
 ^c Centre d'Elaboration de Matériaux et d'Etudes Structurales, CNRS UPR 8011, 29 rue J. Marvig, BP 94347, Toulouse cedex 4 31055, France
 ^d Université de Toulouse, UPS, F-31055 Toulouse, France

12 Abstract

1

2

5

7

9

10

11

We investigate the influence of elastic properties of point defects on dislocation climb under stress and irradiation. For this purpose, elastic dipole tensors and diaelastic polarizabilities are evaluated in aluminum for vacancies and selfinterstitial atoms in their stable and saddle configurations, using density functional theory calculations. These parameters are introduced in an object kinetic Monte-Carlo code and a continuous diffusion model to estimate the stress dependence of dislocation climb, using a dipole of straight dislocations. We show that both parameters have an influence on absorption of point defects under stress, in agreement with previous analytical models. However, the effect of dipole tensor is found only 5 times larger than polarizability, whereas models predict a factor up to 30. In addition, including polarizability reverses the stress angular dependence when a uniaxial stress is applied orthogonal to the dislocation line, so in general polarizability cannot be ignored for simulations under applied stress. Further comparison with analytical models shows that they give a good description of angular dependence, provided saddle point configuration of point defects is not too anisotropic. For vacancies, which are strongly anisotropic in their saddle configuration, models fail to reproduce quantitatively lattice effects on stress angular dependence observed in simulations. Calculations show that dislocation climb velocity under irradiation is expected to be the highest if the

October 10, 2022

Preprint esybmitted totElsevier

Email address: thomas.jourdan@cea.fr (T. Jourdan)

stress is approximately orthogonal to the dislocation line, especially along the Burgers vector, and the lowest if the stress is applied close to the $\langle 100 \rangle$ direction with the largest projection on the dislocation line.

- ¹³ Keywords: Diffusion, Object kinetic Monte-Carlo, Irradiation creep,
- ¹⁴ Dislocation climb, SIPA

15 1. Introduction

Under irradiation and applied stress, metallic alloys exhibit a specific defor-16 mation process known as irradiation creep [1, 2]. The associated strain rate, 17 which may be much larger than the one associated to thermal creep, is related 18 to anisotropic microstructural changes. Among them, anisotropic formation 19 and growth of dislocation loops, resulting from the agglomeration of point de-20 fects (self-interstitial atoms, vacancies), have been observed [3, 4, 5, 6, 7, 8]. 21 These processes have been explained by the reorientation of small clusters un-22 der stress [9] and/or the preferred absorption of self-interstitial atoms (SIAs) 23 and vacancies by some dislocation loops, depending on their orientation with 24 respect to the applied stress [10]. Other mechanisms have also been proposed. 25 They are based on climb-assisted glide of dislocations, whose anisotropic char-26 acter may also come from the dependence of climb velocity on stress [11]. 27

Two main models have been developed to explain the preferential climb of 28 some dislocation types under applied stress and irradiation. These two models 29 finely depend on the elastic properties of point defects, which couple to the 30 internal and applied strain fields and result in preferential absorption of point 31 defects at some dislocations. They both describe a point defect through its 32 elastic dipole, a tensor which describes how the point defect energy varies in a 33 strain field. The first model, known as stress induced preferred absorption due 34 to anisotropic diffusion (SIPA-AD)¹ [14, 15, 16, 17], relies on the anisotropy 35 of dipole tensors of point defects in their saddle configuration [18]. Due to 36

¹In some references it is called SIPA-SAPSE (stress induced preferred absorption due to saddle-point shape effect) [12, 13]. This name has the clear advantage to identify the physical

this anisotropy and to the lowering of crystal symmetry by an applied stress, 37 diffusion becomes anisotropic [19, 20]. This anisotropic diffusion is responsible 38 for different absorption "cross-sections" by dislocations and thus for preferred 39 absorption. The second model is the stress induced preferred absorption due 40 to inhomogeneity interaction (SIPA-I). It is also often simply called SIPA, as 41 it was developed first and remains very popular [21, 22, 23, 8]. It relies on the 42 dependence of dipole tensor on local stress, a phenomenon known as diaelastic 43 polarizability [24]. 44

It is customary to quantify the effect of stress on absorption rate of defects 45 by dislocations by calculating absorption efficiencies, which are key quantities in 46 rate theory models. Previous analytical and numerical calculations have shown 47 that in iron and copper, absorption efficiencies under stress exhibit a higher de-48 pendence on elastic dipole anisotropy than on polarizability, so that SIPA-AD 49 could be more than one order of magnitude larger than SIPA-I [14, 12, 16]. This 50 estimate relies on dipole tensors calculated by interatomic potentials, which can 51 differ substantially from dipole tensors evaluated by *ab initio* methods [25]. Sev-52 eral approximations are made for the polarizability of the elastic dipole to make 53 analytical calculations tractable: the four-rank tensors characterizing this polar-54 izability are assumed to be isotropic and identical for defects at stable and saddle 55 positions. In addition, it is unclear what consequences approximations made in 56 analytical models may have on the absorption rates of point defects [16]. For all 57 these reasons, it appears important to evaluate more precisely the amplitudes 58 of SIPA-AD and SIPA-I, *i.e.* the role of elastic dipole anisotropy and diaelastic 59 polarizabilities on absorption efficiencies of point defects by dislocations under 60 stress. 61

In the present work, we use two simulation methods to evaluate these absorption efficiencies in aluminum. The first one is an object kinetic Monte-Carlo

quantity responsible for the anisotropic behavior, since anisotropic diffusion (AD) can come from various physical quantities. However, SIPA-AD seems to be more widely used in the literature, so we keep this name here.

(OKMC) approach, which has already been used to determine absorption effi-64 ciencies without applied stress [26]. The second one is a continuous diffusion 65 model (CDM) [27]. Both methods take into account point defect properties 66 at stable and saddle positions. To obtain a precise value of absorption effi-67 ciencies, dipole and polarizability tensors are extracted from density functional 68 theory (DFT) calculations. Aluminum is chosen because it is nearly elastically 69 isotropic, so that isotropic elasticity can be used conveniently to predict absorp-70 tion efficiencies [26]. 71

This article is organized as follows. In section 2 diffusion of point defects under stress is discussed and the existing models of absorption efficiency under stress are shortly reviewed. Dipole tensors and diaelastic polarizabilities are calculated in section 3. Absorption efficiencies of point defects by dislocations are determined by OKMC and CDM and compared to existing models in section 4.

77 2. Diffusion of point defects under stress and existing models of point 78 defect absorption efficiency

79 2.1. Diffusion under stress

The migration of point defects to dislocations depends on their interaction with the elastic field created by dislocations and the applied stress. A point defect can be adequately described as an elastic dipole Π_{ij} [28, 29], which depends on the local strain field if it is polarizable (summation over repeated indexes is implied):

$$\Pi_{ij}(\boldsymbol{\varepsilon}) = P_{ij} + \alpha_{ijkl}\varepsilon_{kl},\tag{1}$$

where $P_{ij} = \Pi_{ij}(0)$ is the elastic dipole without any effect of stress, α_{ijkl} the diaelastic polarizability and ε_{ij} the local strain field at the position of the point defect. The associated interaction energy can be expressed as [30]:

$$E = -P_{ij}\varepsilon_{ij} - \frac{1}{2}\varepsilon_{ij}\alpha_{ijkl}\varepsilon_{kl}.$$
 (2)

Elastic dipoles and polarizabilities are in general different at stable and saddle positions. In the following, superscript "s" means that a quantity is taken at saddle position. Dederichs and Schroeder have shown that the point defect flux can be written as a function of a renormalized diffusion tensor [20]

$$\tilde{D}_{ij}(\boldsymbol{r}) = \frac{1}{4} D_0 \sum_{\boldsymbol{h}} \hat{h}_i \hat{h}_j \exp\left(-\frac{E^{\mathrm{s},\boldsymbol{h}}(\boldsymbol{r})}{k_{\mathrm{B}}T}\right),\tag{3}$$

where $E^{s,h}(\mathbf{r})$ is the interaction energy as given by Eq. (2) for a point defect 93 initially located at \boldsymbol{r} and performing a jump \boldsymbol{h} with associated unit vector $\hat{\boldsymbol{h}}, D_0$ 94 is the diffusion coefficient without stress, $k_{\rm B}$ the Boltzmann constant and T the 95 temperature. The strain field in the interaction energy is taken at the location 96 of the saddle point, which in the present case is r + h/2. The summation 97 is performed on all nearest neighbors. The stress free diffusion coefficient is 98 $D_0 = \kappa \nu_0 a^2 \exp\left(-E_0^{\rm m}/k_{\rm B}T\right)$, where $\kappa = 1$ for a vacancy and $\kappa = 2/3$ for a 99 (100)-split dumbbell SIA. In this expression, a is the lattice parameter of the 100 fcc matrix, ν_0 and $E_0^{\rm m}$ the attempt frequency and migration energy, respectively. 101 Using a Taylor expansion to second order in strain of the diffusion coeffi-102 cient, Woo has clearly shown that different terms contribute to stress induced 103 preferential absorption [16]. Even though in the present work this expansion is 104 not used, it is useful to recall it to make the link with existing models. Let ε_{ij} be 105 the sum of an applied strain $\varepsilon^{\rm a}_{ij}$ and an internal strain $\varepsilon^{\rm d}_{ij}$ due to a dislocation, 106 which is assumed to weakly vary over distance a, so that $\varepsilon_{ij}^{d}(\mathbf{r} + \mathbf{h}/2) \approx \varepsilon_{ij}^{d}(\mathbf{r})$. 107

 $_{108}$ Inserting (2) into (3) leads to

$$\begin{split} \tilde{D}_{ij}(\boldsymbol{r}) &\approx \underbrace{D_{0}\delta_{ij}}_{1 \text{ - stress free diffusion}} + \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}P_{kl}^{\mathbf{s},\boldsymbol{h}}\varepsilon_{kl}^{\mathrm{d}}(\boldsymbol{r})}_{2 \text{ - EID, first order}} \\ &+ \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}P_{kl}^{\mathbf{s},\boldsymbol{h}}\varepsilon_{kl}^{\mathrm{a}}}_{3 \text{ - elastodiffusion, SIPA-AD (Woo)}} \\ &+ \frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}(\underbrace{\alpha_{klmn}^{\mathbf{s},\boldsymbol{h}}}_{4 \text{ - SIPA-I}} + \underbrace{\frac{1}{k_{\mathrm{B}}T}P_{kl}^{\mathbf{s},\boldsymbol{h}}P_{mn}^{\mathbf{s},\boldsymbol{h}}}_{5 \text{ - SIPA-AD (Dederichs)}})\varepsilon_{kl}^{\mathrm{a}}\varepsilon_{mn}^{\mathrm{d}}(\boldsymbol{r}) \\ &+ \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}\left(\frac{1}{2}\alpha_{klmn}^{\mathbf{s},\boldsymbol{h}} + \frac{1}{2}\frac{1}{k_{\mathrm{B}}T}P_{kl}^{\mathbf{s},\boldsymbol{h}}P_{mn}^{\mathbf{s},\boldsymbol{h}}\right)\varepsilon_{kl}^{\mathrm{d}}(\boldsymbol{r})\varepsilon_{mn}^{\mathrm{d}}(\boldsymbol{r}) \\ &+ \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}\left(\frac{1}{2}\alpha_{klmn}^{\mathbf{s},\boldsymbol{h}} + \frac{1}{2}\frac{1}{k_{\mathrm{B}}T}P_{kl}^{\mathbf{s},\boldsymbol{h}}P_{mn}^{\mathbf{s},\boldsymbol{h}}\right)\varepsilon_{kl}^{\mathrm{d}}(\boldsymbol{r})\varepsilon_{mn}^{\mathrm{d}}(\boldsymbol{r}) \\ &+ \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}\left(\frac{1}{2}\alpha_{klmn}^{\mathbf{s},\boldsymbol{h}} + \frac{1}{2}\frac{1}{k_{\mathrm{B}}T}P_{kl}^{\mathbf{s},\boldsymbol{h}}P_{mn}^{\mathbf{s},\boldsymbol{h}}\right)\varepsilon_{kl}^{\mathrm{d}}\varepsilon_{mn}^{\mathrm{d}}(\boldsymbol{r}) \\ &+ \underbrace{\frac{1}{4}D_{0}\frac{1}{k_{\mathrm{B}}T}\sum_{\boldsymbol{h}}\hat{h}_{i}\hat{h}_{j}\left(\frac{1}{2}\alpha_{klmn}^{\mathbf{s},\boldsymbol{h}} + \frac{1}{2}\frac{1}{k_{\mathrm{B}}T}P_{kl}^{\mathbf{s},\boldsymbol{h}}P_{mn}^{\mathbf{s},\boldsymbol{h}}\right)\varepsilon_{kl}^{\mathrm{d}}\varepsilon_{mn}^{\mathrm{d}}. \end{split}$$

7 - elastodiffusion, second order

The first term corresponds to the diffusion tensor in the absence of stress. The 109 second term, which is related to the elastic interaction difference (EID) for 110 SIAs and vacancies, is responsible for the dislocation bias [31] to first order 111 (second order is the sixth term, it is always neglected). The third term is the 112 classical elastodiffusion term [20]. It has been identified by Woo as the main 113 contribution to SIPA [13, 16], called SIPA-AD. The fourth and fifth terms couple 114 the dislocation and applied strains and thus also lead to SIPA. The contribution 115 of polarizability corresponds to SIPA-I effect [21, 22, 23], whereas the product 116 of dipole tensors is the SIPA-AD effect as initially considered by Dederichs and 117 Schroeder [20]. In numerical simulations based on dipole tensor anisotropy, both 118 the third and fifth terms are included since the diffusion coefficient is kept in its 119 initial form (3) [15]. Finally, the sixth and seventh terms are second order terms 120 for EID and elastodiffusion. Although the latter can in principle contribute to 121 SIPA, it has been ignored in previous studies based on polarizabilities, which 122 all relied on analytical developments. Only the fourth term was considered. 123 However, here again, the second part of this term is present in numerical studies 124

¹²⁵ using anisotropic dipole tensors.

¹²⁶ 2.2. Models of point defect absorption efficiency under stress

In the framework of rate theory, the effect of stress on point defect absorp-127 tion rate by dislocations is quantified by the so-called "absorption efficiencies". 128 These quantities relate the absorption rate of point defects to their average con-129 centration in the matrix. They are obtained by solving the diffusion problem 130 around a sink, usually at stationary state [32, 33, 34, 35, 36]. Analytical ex-131 pressions of absorption efficiencies can be obtained only with simple geometries 132 and simplified description of point defect properties. Taking into account the 133 full complexity of Eq. (4) necessarily requires numerical simulations, as those 134 performed in the present work. 135

Heald and Speight have given an expression for the absorption efficiency of defects by dislocations under a tensile stress of magnitude σ , if among terms 3 to 7 in Eq. (4) only the fourth one is taken into account (SIPA-I) [23]. They assume that the polarizability tensor is the same at stable and saddle points and that it is isotropic, *i.e.*

$$\alpha_{ijkl} = \left(\alpha^{K} - \frac{2}{3}\alpha^{\mu}\right)\delta_{ij}\delta_{kl} + \alpha^{\mu}\left(\delta_{ik}\delta_{jl} + \delta_{il}\delta_{jk}\right),\tag{5}$$

where α^{K} and α^{μ} are the bulk and shear polarizabilities [37]. This approximation amounts to considering the defect as an isotropic inhomogeneous Eshelby inclusion in the matrix. The dipole tensor is also assumed to be the same at stable and saddle points and is considered isotropic, *i.e.* $P_{ij} = P\delta_{ij}$. Woo has shown that the expression of Heald and Speight can be cast under the following form (HSW model) [38]:

$$Z^{\mathrm{I}}(\boldsymbol{\sigma}) = Z^{0} \left(1 + \frac{\Delta Z^{\mathrm{I}}(\boldsymbol{\sigma})}{Z^{0}} \right), \tag{6}$$

147 with

$$\frac{\Delta Z^{\mathrm{I}}(\boldsymbol{\sigma})}{Z^{0}} = \frac{Z^{0}}{2\pi} \frac{\delta L(\boldsymbol{\sigma})}{L^{0}} \tag{7}$$

$$Z^{0} = \frac{2\pi}{\ln\left(\frac{4R}{|L^{0}|e^{\gamma}}\right)} \tag{8}$$

$$L^{0} = \frac{Pb}{2\pi} \frac{1-2\nu}{1-\nu} \frac{1}{k_{\rm B}T}$$
(9)

$$\frac{\delta L(\boldsymbol{\sigma})}{L^0} = \frac{\sigma}{\mu} \left[\frac{(1-2\nu)\alpha^K}{2(1+\nu)P} + \frac{\alpha^\mu}{3(1-2\nu)P} \left(-(1+\nu) + 3\nu(\boldsymbol{s}\cdot\boldsymbol{l})^2 + 3(\boldsymbol{s}\cdot\boldsymbol{b})^2 \right) \right]$$
(10)

(note that the 2π factor in Eq. (7) is missing in the expression of Woo). Z^0 148 is the absorption efficiency without applied stress. In Eqs. (8)-(10), ν is the 149 Poisson's ratio, μ is the shear modulus, **b** is the Burgers vector $(b = |\mathbf{b}|)$, **l** is 150 the dislocation line direction, γ is the Euler's constant ($\gamma \approx 0.577$) and R is 151 the half-distance between dislocations, calculated as $R = (\pi \rho_d)^{-1/2}$ with ρ_d the 152 dislocation density. The uniaxial stress is applied along s, so that $\sigma_{ij} = \sigma s_i s_j$. 153 Eqs. (6) to (10) are often given with different notations, considering the defect 154 as an Eshelby inhomogenous inclusion. The link between the two formalisms is 155 recalled in Appendix A. For the sake of completeness, we note that an expression 156 with a similar dependence on stress orientation, in $(\boldsymbol{s} \cdot \boldsymbol{l})^2$ and $(\boldsymbol{s} \cdot \boldsymbol{b})^2$, was 157 obtained by Wolfer and Ashkin [37]. 158

With this model, the stress direction leading to the highest absorption efficiency depends on the sign of α^{μ}/P (Eq. (10)). For an SIA in fcc metals, it is known that in its stable position, $\alpha^{\mu} > 0$ and P > 0 [39], so the model predicts that SIAs are more absorbed by a dislocation if the tensile stress is along the Burgers vector. For a vacancy, it is assumed in the literature that $\alpha^{\mu} > 0$ [23, 22], but P < 0, so the reverse behavior is expected.

Later, SIPA due to elastodiffusion (SIPA-AD) was investigated analytically by Skinner and Woo [13], Woo [16], and Borodin and Ryazanov [17]. The most general formula was derived by Borodin and Ryazanov. They showed that if only the three first terms in Eq. (4) are retained, and if the deviatoric part of the dipole tensor at saddle point is small, the absorption efficiency of a defect 170 can be written as

$$Z^{\rm AD}(\boldsymbol{\sigma}) = Z^0 \left(1 + \frac{\Delta Z^{\rm AD,0}}{Z^0} + \frac{\Delta Z^{\rm AD,hydro}(\boldsymbol{\sigma})}{Z^0} + \frac{\Delta Z^{\rm AD,dev}(\boldsymbol{\sigma})}{Z^0} \right).$$
(11)

Contrary to the SIPA-I model described above, in this model, hereafter called 171 B&R model, the defect has different properties at stable and saddle positions. 172 The absorption efficiency Z^0 is still defined by Eqs. (8) and (9), but P is now re-173 lated to saddle point properties, *i.e.* $P = P^{s} = \text{Tr}(\mathbf{P}^{s})/3$. Z^{0} thus corresponds 174 to the absorption of an isotropic defect at saddle point. Saddle point anisotropy 175 can have an influence on absorption efficiency even in the absence of applied 176 stress [15, 40, 13, 17, 26, 41], this is taken into account through $\Delta Z^{AD,0}$. The 177 effect of stress on absorption efficiency can be decomposed into an hydrostatic 178 term $\Delta Z^{\text{AD,hydro}}$ depending only on Tr ($\boldsymbol{\sigma}$), and a deviatoric term $\Delta Z^{\text{AD,dev}}$. 179 Only the latter is of interest here, as we focus on the difference of absorption 180 efficiencies for different orientations of applied stress. For a uniaxial stress, it 181 reads [17, 42] 182

$$\frac{\Delta Z^{\text{AD,dev}}(\boldsymbol{\sigma})}{Z^0} = -\frac{\sigma}{4\mu} \frac{P^{\text{s}}}{k_{\text{B}}T} \left\{ d^{(2)} \left[(\boldsymbol{s} \cdot \boldsymbol{l})^2 - \frac{1}{3} \right] + d^{(3)} \sum_{p=1}^3 \left[(\boldsymbol{e}_p \cdot \boldsymbol{l})^2 (\boldsymbol{e}_p \cdot \boldsymbol{s})^2 - \frac{1}{9} \right] \right\}$$
(12)

where e_p (p = 1, 2, 3) are the unit vectors along the crystallographic axes. Factors $d^{(2)}$ and $d^{(3)}$ are related to the components of dipole tensors at saddle point. In an fcc structure, the dipole tensor of a defect jumping along [110] is of the form

$$\boldsymbol{P}^{s} = \begin{pmatrix} P_{11}^{s} & P_{12}^{s} & 0\\ P_{12}^{s} & P_{11}^{s} & 0\\ 0 & 0 & P_{33}^{s} \end{pmatrix}.$$
 (13)

We then have $d^{(2)} = P_{12}^{\rm s}/P^{\rm s}$ and $d^{(3)} = (P_{11}^{\rm s} - P_{33}^{\rm s})/(2P^{\rm s}) - P_{12}^{\rm s}/P^{\rm s}$.

It appears from Eq. (12) that the absorption efficiency does not depend on the orientation of uniaxial stress with respect to the Burgers vector, unlike SIPA-I. It is generally accepted that what is important for SIPA-AD is the orientation of stress with respect to the dislocation line direction l, as shown in ¹⁹² the simplified model of Woo [16]:

$$\frac{\Delta Z^{\text{AD,dev}}(\boldsymbol{\sigma})}{Z^0} = \frac{3\sigma}{8\mu} \frac{P^{\text{s}}}{k_{\text{B}}T} \left(1 - \frac{P^{\text{s}}_{1}}{P^{\text{s}}}\right) \left[(\boldsymbol{s} \cdot \boldsymbol{l})^2 - \frac{1}{3} \right].$$
(14)

This expression corresponds to Eq. (12) if $l = e_p$ for a given p, except that P_{11}^{s} 193 in Eq. (12) is replaced by the eigenvalue P_1^s associated to the eigenvector along 194 the jump direction (in practice P_{11}^{s} and P_{1}^{s} are very close, since $P_{1}^{s} = P_{11}^{s} + P_{12}^{s}$ 195 and $P_{12}^{s} \ll P_{11}^{s}$). For vacancies, $P^{s} < 0$ and $P_{1}^{s}/P^{s} > 1$ [43, 26], so a tensile 196 stress applied along the dislocation line increases the absorption efficiency. For 197 SIAs, $P^{\rm s} > 0$ and $P_1^{\rm s}/P^{\rm s} > 1$, so the reverse behavior is expected. We note 198 however that in the general case (Eq. (12)), it is clear that the orientation of 199 stress with respect to crystallographic axes also plays a role. 200

Expressions for SIPA-AD and SIPA-I use only some terms in Eq. (4). In re-201 ality, all terms from 3 to 7 contribute to absorption efficiency modification under 202 stress. As shown by Savino and Tomé [14], the third term, as a first-order term, 203 should give the highest contribution. However, their results were obtained with 204 crude estimates of polarizabilities and values of dipole tensors calculated by in-205 teratomic potentials. In addition, as shown in the previous paragraphs, various 206 approximations underlie the analytical derivations. That is why, in the follow-207 ing, we evaluate the dipole tensors and polarizabilities for both stable and saddle 208 configurations by DFT and introduce them into an OKMC code and a CDM 209 model, which take into account the full complexity of diffusion under stress. 210 We determine the relative importance of dipole anisotropy and polarizability by 211 comparing these calculations to calculations without polarizability. The validity 212 of expressions (7)-(10) and (12) is discussed, based on our simulation results. 213

214 3. Point defect properties

215 3.1. Method

Point defect properties can be calculated by atomistic simulations, from the energy difference between two simulation boxes containing a point defect, one with applied homogeneous deformation ε and the other one without deformation. Following Eq. (2), it reads, for a box of volume V [44, 29],

$$\Delta E(\boldsymbol{\varepsilon}) = \frac{1}{2} \varepsilon_{ij} C_{ijkl} \varepsilon_{kl} V - P_{ij} \varepsilon_{ij} - \frac{1}{2} \varepsilon_{ij} \alpha_{ijkl} \varepsilon_{kl}.$$
 (15)

The first term corresponds to the homogeneous deformation of the perfect crystal. It can be calculated separately with a dedicated simulation of a box without defect and subtracted from ΔE to retain only the contribution of the point defect. By fitting Eq. (15) without bulk contribution on calculations performed at different deformation levels, for different deformation types (shear, isotropic dilatation, etc.), it is possible to extract point defect dipole and polarizability tensors.

Another method consists in using the average residual stress on the simulation box [44, 29]:

$$\sigma_{ij}(\boldsymbol{\varepsilon}) = \frac{1}{V} \frac{\partial \Delta E}{\partial \varepsilon_{ij}} = C_{ijkl} \varepsilon_{kl} - \frac{1}{V} \left(P_{ij} + \alpha_{ijkl} \varepsilon_{kl} \right).$$
(16)

Elastic dipoles are readily obtained from simulations with zero applied deformation [45], after subtracting the spurious stress in the perfect simulation box [29]. Polarizabilities can be extracted from a linear fit of the stress as a function of the deformation level, after subtraction of the contribution of the perfect crystal. If the dipole component is also deducted, the quantity $\Delta \sigma_{ij}(\varepsilon) = -\alpha_{ijkl}\varepsilon_{kl}/V$ is obtained.

To evaluate point defect properties in aluminum, DFT calculations are per-235 formed with VASP code [46, 47, 48, 49] using the projector augmented-wave 236 (PAW) method [50, 51]. Calculations are performed including the s states 237 [Ne]3s²3p¹. The exchange correlation energy is evaluated using the Perdew-238 Burke-Ernzerhof (PBE) generalized gradient approximation (GGA). The plane 239 wave energy cutoff is set to 400 eV. Brillouin zone integration is performed 240 with a Methfessel-Paxton broadening of 0.4 eV. Supercells with an SIA or a 241 vacancy contain 256 ± 1 atoms. With such simulation cells, a dense shifted 242 Monkhorst-Pack k-point mesh grid of $8 \times 8 \times 8$ points is necessary to obtain 243 converged results, in agreement with previous results [52]. Each configuration 244

is relaxed using the conjugate gradient technique. The climbing image nudged
elastic band method (CI-NEB) [53] using 7 images is used in order to find saddle
points. A calculation is considered as converged when the forces on each atom
are lower than 0.002 eV/Å.

In the present study, dipole tensors are calculated with the stress method 249 (Eq. (16)). Simulations with interatomic potentials with different supercell sizes, 250 reported in supplementary material, show that the error on dipole tensor compo-251 nents due to the interaction between the point defect and its periodic images [25] 252 is less than 1% (Fig. S1 and Table S1). Both energy and stress methods were 253 tested to determine polarizabilities. The convergence with the number of k-254 points turned out to be faster with the stress method, in agreement with previ-255 ous observations [54]. In addition, the stress method requires fewer deformation 256 types to extract polarizabilities, since the different stress components are related 257 to different combinations of α_{ijkl} coefficients. For these two reasons the stress 258 method is used. A list of the deformation types, with the corresponding values of 259 $-V\Delta\sigma_{ij}(\boldsymbol{\varepsilon}) = \alpha_{ijkl}\varepsilon_{kl}$, is given in Appendix B. Although the first deformation 260 is not necessary to determine coefficients for cubic and tetragonal symmetries, it 261 is calculated in order to check consistency of coefficients calculated by different 262 deformations. It also gives an estimate of the error on the coefficients, which 263 can roughly be estimated to a few eV. An additional source of error comes from 264 the interaction of the point defect with its periodic images [62]. Simulations 265 with interatomic potentials show that the error on polarizability tensor compo-266 nents with supercells of 256 atoms is less than 10 %, except one component for 267 which it reaches 17 % (Fig. S2 and Table S1). Calculation of polarizabilities 268 at saddle points is computationally demanding, since a NEB calculation must 269 be performed for each deformation level of each deformation type. At least 5 270 deformation levels are used to perform the fit. 271

272 3.2. Results

Dipole and polarizability tensors are given in Table 1. Dipole tensor values are slightly different from a previous DFT study [26], due to different DFT settings and in particular denser k-point meshes used here. They are in good agreement with recent DFT calculations performed on the vacancy [55]. The relaxation volumes, deduced from the dipole tensor values through

$$\Delta V^{\rm r} = \frac{\operatorname{Tr} \boldsymbol{P}}{3K},\tag{17}$$

where $K = (C_{11} + 2C_{12})/3$ is the bulk modulus, are also presented in Table 1. Altogether the values agree reasonably well with experiments, although the absolute value of the relaxation volume of the vacancy in its stable configuration is larger than the experimental value measured at 4 K. The tetragonal deviation from a cubic dipole tensor for the SIA in its stable configuration is in excellent agreement with the experimental value $P_{11} - P_{22} = 1.1 \pm 0.3$ eV [56].

As can be seen from Eq. (15), introducing polarizable point defects in a material leads to a variation of its elastic constants:

$$\Delta C_{ijkl} = -\frac{x}{\Omega} \alpha_{ijkl},\tag{18}$$

where x is the atomic fraction of defects and Ω the atomic volume. This can be written under the more convenient form:

$$\frac{\Delta C_{ijkl}}{xC_{ijkl}} = -\frac{1}{\Omega C_{ijkl}} \alpha_{ijkl}.$$
(19)

Although α_{ijkl} has a tetragonal symmetry for SIAs, it is not possible to measure all components of the tensor experimentally. Assuming that SIA variants are equally distributed in the material, only data related to cubic symmetry can be extracted. Therefore it is possible to measure two shear polarizabilities

$$\alpha_{44}^* = \frac{1}{3} \left(\alpha_{44} + 2\alpha_{55} \right) \tag{20}$$

$$\alpha'^* = \frac{1}{3} \left(\frac{\alpha_{11} - \alpha_{12}}{2} + \frac{\alpha_{22} - \alpha_{12}}{2} + \frac{\alpha_{22} - \alpha_{23}}{2} \right)$$
(21)

²⁹² and a bulk polarizability

$$\alpha^{K} = \frac{1}{3} \left(\frac{1}{3} (\alpha_{11} + 2\alpha_{12}) + \frac{2}{3} (\alpha_{22} + \alpha_{12} + \alpha_{23}) \right).$$
(22)

From Eq. (19) it is then possible to compute the influence of defects on C_{44} , $C' = (C_{11} - C_{12})/2$ and K. DFT results in Tab. 1 show that SIAs contribute

much more to the change of elastic constants than vacancies, in agreement 295 with experimental results [57]. Vacancies make the material more compliant 296 in compression and in shear, while SIAs are compliant in shear and stiff in 297 compression. These variations are consistent with trends inferred from simple 298 arguments in early works on SIPA-I [23]. The fact that SIAs are compliant in 299 shear, which is not so intuitive, was proved with analytical models and atomistic 300 calculations [58]. Experimental measurements also support this result. The 301 variation in the two shear moduli, C_{44} and C', was measured in aluminum after 302 electron irradiation at low temperature, where only Frenkel pairs are created 303 (Tab. 1). Negative values were obtained, in agreement with present results. 304 We note also that $|\Delta C_{44}/xC_{44}| > |\Delta C'/xC'|$, which has been shown to be 305 typical of fcc metals containing 100-dumbbells [58, 57]. Finally and perhaps 306 most importantly, the magnitude of the change of shear moduli due to both 307 vacancies and SIAs agrees well with experimental results. The change in bulk 308 modulus upon introduction of point defects has not been measured in aluminum 309 but it is expected to be small, following results obtained in Cu [59, 60]. This is 310 confirmed by our calculations. 311

We end this section with a comment on the calculation of polarizabilities 312 with interatomic potentials. Early calculations were made with simple pair 313 potentials for stable [58] and saddle [30, 61] configurations. The obtained polar-314 izabilities were found consistent with the variation of elastic constants measured 315 experimentally [58, 30]. However, later simulations in Cu with more physical 316 potentials were shown to produce results at variance with experiments [62], with 317 values of opposite signs. We encountered similar problems with potentials in 318 aluminum, which highlights the need for DFT calculations to evaluate polariz-319 abilities. 320

Table 1: Dipole and polarizability tensors of vacancies and SIAs in their stable and saddle configurations. Entries which are not filled are zero by symmetry. Relaxation volumes and change of elastic constants due to defects, deduced from dipole tensors and polarizabilities, respectively, are compared to experimental values. Elastic constants determined by DFT are $C_{11} = 111.4$ GPa, $C_{12} = 60.7$ GPa and $C_{44} =$ 33.1 GPa.

	vacancy (stable)	vacancy (saddle)	SIA (stable)	SIA (saddle)
		$([100] \rightarrow [010])$	([100])	$([100] \rightarrow [010])$
$P_{11} ({\rm eV})$	-2.49	-2.15	18.71	18.57
P_{22} (eV)	$= P_{11}$	$= P_{11}$	17.80	$= P_{11}$
$P_{33} ({\rm eV})$	$= P_{11}$	1.96	$= P_{22}$	18.40
P_{12} (eV)		-0.22		1.45
$\alpha_{11} \ (eV)$	23	41	-10	4
$\alpha_{33} \ (eV)$	$= \alpha_{11}$	-3	-13	-8
$\alpha_{44} \ (eV)$	4	7	103	73
$\alpha_{55}~(\mathrm{eV})$	$= \alpha_{44}$	$= \alpha_{44}$	41	$= \alpha_{44}$
$\alpha_{66} \ (eV)$	$= \alpha_{44}$	15	$= \alpha_{55}$	62
$\alpha_{36} \ (eV)$		9		0
$\alpha_{16} \ (eV)$		$^{-1}$		-12
$\alpha_{45} \ (eV)$		10		25
$\alpha_{23} \ (eV)$	$= \alpha_{12}$	$= \alpha_{13}$	-45	$= \alpha_{13}$
$\alpha_{13} \ (eV)$	$= \alpha_{12}$	2	$= \alpha_{12}$	-56
$\alpha_{12} \ (eV)$	13	19	-60	-71
$\Delta V^{\mathrm{r}}/\Omega$ (sim.)	-0.31	-0.10	2.27	
$\Delta V_{\rm I} / \Omega$ (or)	$-0.05\pm0.05^{\rm (a)}$	$-0.19^{(d)}$	$1.9\pm0.2^{\rm (a,c)}$	
$\Delta V / \Omega (exp.)$	$-0.36^{(b)}$			
$\frac{\Delta C_{44}}{xC_{44}}$ (sim.)	-1.2		-18.1	
$\frac{\Delta C_{44}}{xC_{44}}$ (exp.) ^(e)			-23 ± 2	
$\frac{\Delta C'}{xC'_{\prime\prime}}$ (sim.)	-1.9		-8.2	
$\frac{\Delta C'}{x C'_{\tau}} $ (exp.) ^(e)			-13 ± 2	
$\frac{\Delta K}{xK}$ (sim.)	-2		5	

^(a) Measurement at 4 K, Reference [63].

^(b) Measurement at 700 K, Reference [64].

^(c) Reference [65].

^(d) Reference [66], using formation volume of Ref. [64].
^(e) After subtraction of the anharmonic effect due to volume expansion [57]. This value corresponds to the sum of SIA and vacancy contributions, but it is often considered that vacancy contribution is small [39, 57], which is confirmed by measurements on quenched samples [67].

4. Effect of stress orientation on point defect absorption by dislocations

323 4.1. Methods

In this part, we evaluate the absorption efficiencies of point defects by dis-324 locations in the configuration shown in Fig. 1. The system contains two dis-325 locations of opposite Burgers vectors $\mathbf{b} = \pm a/2[10\overline{1}]$ and line direction $\mathbf{l} = b$ 326 $1/\sqrt{6}[\overline{1}2\overline{1}]$. The vector normal to the glide plane is $n = 1/\sqrt{3}[111]$. The lattice 327 is rotated to align the dislocations along the direction u_z of the orthorhombic 328 box and the Burgers vectors along u_x . The dimension of the system is d along 329 and 2d along x, with d = 100 nm, and the dislocations are located at d/2 and 330 3d/2 along x. This corresponds to a dislocation density $\rho_{\rm d} = 10^{14} {\rm m}^{-2}$, which 331 is typical of steady state dislocation densities of irradiated microstructures [68]. 332 Along z, the system consists of a thin slab of 1 nm. Periodic boundary condi-333 tions are used in the three directions. This arrangement of dislocations was used 334 in a previous study [26], it ensures a proper convergence of the strain field when 335 the contribution of dislocations in periodic replica is taken into account [69], if 336 the strain field is evaluated with isotropic elasticity. It has been checked pre-337 viously that in aluminum, using isotropic elasticity has a negligible effect on 338 absorption efficiencies [26], so we use this approximation here. This also per-339 mits to increase the computational efficiency of OKMC simulations. The shear 340 modulus is $\mu = 26$ GPa and the Poisson's ratio is $\nu = 0.35$ [26]. Other disloca-341 tion arrangements could have been chosen; with such dislocation densities they 342 would give slightly different values of absorption efficiencies [35]. However, the 343 dependence of absorption efficiencies on stress orientation is expected to be the 344 same. 345

To determine absorption efficiencies, vacancies and SIAs are considered separately. Point defects are uniformly generated in the system and they are absorbed if they reach one of the cylinders of radius $r_c = 2b$ centered on dislocations. The mean field equation describing the evolution of point defect average



Figure 1: System simulated containing a dipole of straight dislocations. A tensile stress σ is applied along s, given by the two angles (θ, φ) .

 $_{350}$ concentration \bar{C} is

$$\frac{\mathrm{d}\bar{C}}{\mathrm{d}t} = G - Z\rho_{\mathrm{d}}D_{0}\bar{C},\tag{23}$$

where G is the creation rate. The absorption efficiency is deduced at steady state from the measurement of \overline{C} :

$$Z = \frac{G}{\rho_{\rm d} D_0 \bar{C}}.\tag{24}$$

A convenient method to determine \bar{C} is object kinetic Monte-Carlo [26]. Point defects are introduced at a constant rate in the simulation box. They perform atomic jumps until they are absorbed by one of the dislocations. For a point defect located at r, jump frequencies are calculated for each jump h, using the following expression:

$$\Gamma^{\boldsymbol{h}}(\boldsymbol{r}) = \nu_0 \exp\left(-\frac{E_0^{\mathrm{m}} + E^{\mathrm{s}}(\boldsymbol{r} + \boldsymbol{h}/2) - E^{\mathrm{e}}(\boldsymbol{r})}{k_{\mathrm{B}}T}\right),\tag{25}$$

where, as in section 2, ν_0 and $E_0^{\rm m}$ are the attempt frequency and the migration energy without elastic interactions, $E^{\rm e}$ and $E^{\rm s}$ are the interaction energies with the local strain field at stable and saddle points, respectively (Eq. (2)). Events (defect jumps and creation of point defects) are chosen following the residence time algorithm [70, 71]. Transition of SIAs to $\langle 110 \rangle$ crowdion configuration, highlighted recently in copper under high local shear strain [72], is not considered. More details on OKMC simulations can be found in Ref. [26].

For a given creation rate, it is possible to determine Z by calculating the average number of point defects in the simulation box at steady state (Eq. (24)). The physical time of the simulations is chosen to ensure the convergence of Z. To provide a confidence interval, the standard deviation is computed with a blockaveraging procedure [73]. On all graphs, the error bars in figures correspond to the standard deviation.

An alternative to OKMC is the continuous diffusion model (CDM), as described in Ref. [27]. This approach has been shown to produce results in close agreement with reference OKMC simulations; in particular, it can properly handle the interaction of point defects with sinks in their stable and saddle positions, as explicitly done in OKMC. The equation to be solved is based on the expression of the renormalized diffusion tensor given in Eq. (3):

$$G - \boldsymbol{\nabla} \cdot \boldsymbol{J} = 0, \tag{26}$$

377 with

$$\boldsymbol{J}(\boldsymbol{r}) = -\tilde{\boldsymbol{D}}(\boldsymbol{r})\boldsymbol{\nabla}\boldsymbol{u}(\boldsymbol{r}). \tag{27}$$

In this equation, u is a renormalized concentration, which accounts for the concentrations of the different configurations of defects in their stable position (for SIAs) [20, 27]. Contrary to OKMC, CDM is a local approach, *i.e.* it amounts to taking E^{s} in Eq. (25) at r instead of r + h/2. In practice, for weakly varying elastic fields, this approximation is valid. CDM calculations are similar to phase field calculations in this context [41].

Since it is deterministic in nature, CDM produces results which are free 384 of statistical error. However, the finite element solving of the continuity equa-385 tion (26) may be quite CPU and memory demanding for large three-dimensional 386 systems, as fine meshing is required near the sink where concentrations and elas-387 tic fields vary steeply. Therefore, this method is especially useful for systems 388 which are invariant along at least one direction. This is the case of the con-389 figuration shown in Fig. 1, which is invariant along z. Although absorption 390 efficiencies can be obtained with a two-dimensional system, we use a thin slab 391 of 1 nm along z and impose periodic boundary conditions, as in OKMC. 392

In the following, simulations are performed at T = 300 K. A uniaxial tensile stress of 100 MPa is applied along (θ, φ) (Fig. 1). Although this value is rather

high for aluminum (the yield stress of very large grained pure aluminum is 395 around 10 MPa), it permits to obtain a better convergence with OKMC. We 396 have checked, by varying the stress amplitude, that at such levels of stress the 397 absorption efficiency is linear in σ . So the results can easily be extrapolated to 398 lower values of stress. The effect of elastodiffusion is investigated with OKMC, 399 which is our reference method. We check that in this case, CDM produces 400 results in agreement with OKMC. To determine the effect of polarizability, we 401 subtract the absorption efficiencies obtained with and without polarizability. 402 As we need very high accuracy on the absorption efficiencies to perform the 403 subtraction, CDM is used in this case. 404

405 4.2. Results

406 *4.2.1.* SIPA-AD

As explained above, for SIPA-AD the interaction energy of point defects is 407 based solely on elastic dipoles. To evaluate this first mechanism, we start with 408 OKMC simulations. A 3D map representing the influence of tensile stress ori-409 entation on absorption efficiency is shown in Fig. 2. We represent the difference 410 of absorption efficiencies for a uniaxial stress of magnitude σ and a hydrostatic 411 stress with the same value of Tr ($\boldsymbol{\sigma}$), called ΔZ_i^{AD} for SIAs and ΔZ_v^{AD} for va-412 cancies. This quantity corresponds to $\Delta Z^{AD,dev}$ in the decomposition shown in 413 Eq. (11). From Fig. 2 we see that vacancy absorption is increased if the stress 414 is applied close to a direction ($\theta = 30^\circ, \varphi = 90^\circ$). Directions that favor SIA 415 absorption are more or less spread on a strip tilted with respect to the plane 416 orthogonal to the line direction. 417

To provide a more quantitative representation and facilitate the comparison with CDM and B&R model (Eq. (12)), ΔZ^{AD} is plotted in Figs. 3 and 4 as a function of θ , for $\varphi = 0^{\circ}$ (in the slip plane $(\boldsymbol{l}, \boldsymbol{b})$) and $\varphi = 90^{\circ}$ (in the climb plane $(\boldsymbol{l}, \boldsymbol{n})$). Results obtained with CDM are in very good agreement with OKMC, which validates CDM to calculate sink strengths in this configuration. B&R model is able to qualitatively reproduce the effect of stress on absorption efficiency. In particular, the dependence on φ is correctly taken into account,



Figure 2: Difference of absorption efficiency ΔZ^{AD} (see text for the definition) of a straight dislocation dipole in relation to the tensile stress orientation, represented on a unit sphere by a color scale for SIPA-AD mechanism when only P_{ij} is accounted for in the interaction energy. A tensile stress of 100 MPa is applied, scanning space with a 10° step. The dislocation is along [$\overline{121}$] and the Burgers vector is along $\pm [10\overline{1}]$. The SIA results are presented in (a) and (b) and the vacancy results in (c) and (d). For the sake of clarity only one dislocation is schematically represented.

unlike the model of Woo which only depends on θ (not shown). However, the amplitude of ΔZ^{AD} is underestimated with B&R model, especially for the vacancy with a factor up to 3 at $\theta = 30^{\circ}$ and $\varphi = 90^{\circ}$, where the absorption efficiency is maximum.



Figure 3: Difference of absorption efficiency $\Delta Z^{\rm AD}$ (see text for the definition) of a straight dislocation dipole for SIAs as a function of θ (angle between tensile stress and dislocation line l) for SIPA-AD mechanism, with only P_{ij} accounted for in the interaction energy. Results obtained by OKMC and CDM are compared. The analytical B&R model of Eq. (12) is shown in dashed lines. The absorption efficiency is presented for two values of φ : $\varphi = 0^{\circ}$, *i.e.* in a plane containing l and b and $\varphi = 90^{\circ}$, *i.e.* in a plane containing l and n.

429 4.2.2. SIPA-I

To determine the effect of polarizability, absorption efficiencies obtained with dipole tensors only are subtracted from those obtained with both dipole and polarizability tensors taken into account. These quantities are noted ΔZ^{I} . As discussed above, CDM is used for the two calculations to obtain results free from statistical errors.

Absorption efficiencies of SIAs and vacancies are the highest along two different specific directions of applied stress (Fig. 5). Absorption of SIAs is more



Figure 4: Difference of absorption efficiency ΔZ^{AD} (see text for the definition) of a straight dislocation dipole for vacancies as a function of θ (angle between tensile stress and dislocation line l) for SIPA-AD mechanism, with only P_{ij} accounted for in the interaction energy. Results obtained by OKMC and CDM are compared. The analytical B&R model of Eq. (12) is shown in dashed lines. The absorption efficiency is presented for two values of φ : $\varphi = 0^{\circ}$, *i.e.* in a plane containing l and p and $\varphi = 90^{\circ}$, *i.e.* in a plane containing l and n.

efficient if the stress is applied along the Burgers vector, in agreement with early estimates of SIPA-I [21, 23, 38]. The influence of polarizability on vacancy absorption under stress is more surprising. It appears quite similar to the effect of dipole tensor anisotropy, with a direction of preferential absorption along ($\theta = 30^{\circ}, \varphi = 90^{\circ}$). With the existing SIPA-I model, one expects a low absorption rate if the stress is applied along the Burgers vector and a higher absorption rate for other stress orientations.

To provide a more quantitative comparison with HSW model (Eqs. (7)-(10)), which assumes that point defects have the same isotropic properties at stable and saddle positions, the values of dipole tensor P and polarizabilities α^{μ} and α^{K} are deduced from properties of defects in Tab. 1 taken at stable position. P, calculated as Tr (P)/3, is equal to 18.10 eV for SIAs and -2.49 eV for vacancies.



Figure 5: Absorption efficiency increment $\Delta Z^{\rm I}$ of point defects by a straight dislocation dipole in relation to the tensile stress orientation, represented on a unit sphere by a color scale, due to polarizability α_{ijkl} (SIPA-I). Values are obtained by CDM. They result from the difference between absorption efficiencies with P_{ij} and α_{ijkl} considered and with only P_{ij} included. A tensile stress of 100 MPa is applied, scanning space with a 10° step. The dislocation is along [$\overline{121}$] and the Burgers vector is along $\pm [10\overline{1}]$. The SIA results are presented in (a) and (b) and the vacancy results in (c) and (d).

449 Shear polarizability can be expressed as a Voigt average

$$\alpha^{\mu} = \frac{3}{5}\alpha_{44}^{*} + \frac{2}{5}\alpha^{\prime*}, \qquad (28)$$

where α_{44}^* and α'^* are given by Eqs. (20) and (21) respectively. We have $\alpha^{\mu} = 45.6 \text{ eV}$ for SIAs and $\alpha^{\mu} = 4.4 \text{ eV}$ for vacancies. Bulk polarizability, as calculated with Eq. (22), is $\alpha^K = -40.7 \text{ eV}$ for SIAs and $\alpha^K = 16.3 \text{ eV}$ for vacancies.

The effect of SIPA-I is usually discussed for a tensile stress orthogonal to the 454 dislocation line ($\theta = 90^{\circ}$), either along the Burgers vector ($\varphi = 0^{\circ}$) or orthogonal 455 to it ($\varphi = 90^{\circ}$) [23]. The variation of absorption efficiency with φ , with $\theta = 90^{\circ}$, 456 is shown in Figs. 6 and 7 for SIAs and vacancies, respectively. Some terms are 457 dropped in Eq. (6), which may explain why results are shifted with respect to 458 CDM. This shift is not relevant to our purpose. Leaving this aspect aside, the 459 agreement between CDM results and HSW model for $\theta = 90^{\circ}$ is remarkable 460 for the two defects. Results for $\theta = 30^{\circ}$, including the direction where $\Delta Z_{\rm v}^{\rm I}$ is 461 maximum, are also reported in these figures. The analytical solution departs 462 appreciably from CDM, especially for the vacancy. The amplitude of SIPA-I for 463 the vacancy is lower than the result from CDM by more than a factor two. 464

465 4.3. Discussion

466 4.3.1. SIPA-AD

The contribution of intrinsic dipole anisotropy at saddle configuration to 46 SIPA (SIPA-AD) has been discussed by several authors [19, 20, 15, 13, 16, 17]. 468 It was shown that the absorption efficiency is mostly dependent on the direction 469 of uniaxial stress with respect to the dislocation line [15, 13]. Under stress, 470 the diffusion tensor becomes anisotropic, owing to saddle point anisotropy. A 471 dislocation orthogonal to the direction of fastest diffusion will capture more 472 point defects than a dislocation collinear to it, because its "cross section" for 473 defect absorption is higher (the term "cross-section" is only strictly valid for 474 purely 1D diffusion, *i.e.* for an infinitely large effect of stress). Directions of 475 fast diffusion depend on the values of dipole tensor at saddle configuration. 476



Figure 6: Increment of absorption efficiency ΔZ_i^{I} due to polarizability of SIAs, as a function of φ , for two values of θ (30° and 90°). Results are obtained with CDM and compared to HSW model given by Eqs. (7)-(10).

⁴⁷⁷ Vacancies diffuse preferentially in a plane orthogonal to the applied stress [74],
⁴⁷⁸ which explains why vacancy absorption is enhanced when the tensile direction
⁴⁷⁹ is collinear to the dislocation line. The behavior of SIAs is explained with the
⁴⁸⁰ same reasoning [16].

We have seen in Fig. 2 that our simulations and B&R model are in quali-481 tative agreement with these conclusions. However, the direction of maximum 482 absorption of vacancies is shifted by about 30° with respect to the line direc-483 tion in the plane defined by $(\boldsymbol{l},\boldsymbol{n})$ ($\varphi = 90^{\circ}$). Likewise, the strip of maximum 484 absorption for SIAs is tilted, with a maximum at around $\theta = 70^{\circ}$ in the plane 485 $(\boldsymbol{l},\boldsymbol{n})$ and $\theta = 90^{\circ}$ in the plane $(\boldsymbol{l},\boldsymbol{b})$ ($\varphi = 0^{\circ}$). These discrepancies can be ex-486 plained by lattice effects, which are not all taken into account in Woo's approach 487 (Eq. (14)), unlike B&R model (Eq. (12)).488

To explain these results, we consider a uniaxial stress $\sigma_{ij} = \sigma s_i s_j$, with $s_1 = \sin \alpha \cos \beta$, $s_2 = \sin \alpha \sin \beta$, $s_3 = \cos \beta$ the three direction cosines of s in



Figure 7: Increment of absorption efficiency $\Delta Z_{\rm v}^{\rm I}$ due to polarizability of vacancies, as a function of φ , for two values of θ (30° and 90°). Results are obtained with CDM and compared to HSW model given by Eqs. (7)-(10).

⁴⁹¹ the basis ([100], [010], [001]). We have

$$\hat{\varepsilon}_{ij} = \frac{\sigma}{E} \left(s_i s_j (1+\nu) - \nu \delta_{ij} \right), \tag{29}$$

with $E = 2\mu(1 + \nu)$ Young's modulus. We consider a jump along [110], for which the dipole tensor at saddle position is given by Eq. (13). Neglecting the polarizability, the saddle point energy reads

$$E^{\rm s} = -\frac{\sigma}{E} \left(P_{11}(1+\nu)\sin^2\alpha - 2\nu P_{11} + P_{33}(1+\nu)\cos^2\alpha - \nu P_{33} + P_{12}(1+\nu)\sin^2\alpha\sin 2\beta \right).$$
(30)

Given the signs of the dipole tensor components of a vacancy (see Tab. 1), it is clear that the energy is minimum for $\alpha = 0^{\circ}$, *i.e.* for a stress applied along [001]. For the SIA, since $P_{12} > 0$, we must have $\beta = 45^{\circ}$. In addition, with $P_{11} + P_{12} > P_{33}$ the energy is minimum for $\alpha = 90^{\circ}$. This means the stress must be applied along the jump direction to minimize the saddle point energy. As already discussed, to obtain the maximum absorption efficiency by a dislocation, one must favor the jumps which are as orthogonal as possible to

this dislocation. For a dislocation along $l = [\bar{1}2\bar{1}]/\sqrt{6}$, there are two jumps 502 which are orthogonal to the dislocation line, highlighted in red in Fig. 8-(a). 503 These jumps are favored if the stress is applied along [010]. This configuration 504 corresponds to $\theta = 35^{\circ}$, in close agreement with our OKMC and CDM results 505 $(\theta \approx 33^{\circ})$ and B&R results $(\theta = 29^{\circ})$. The absorption rate of SIAs should be 506 large if the stress is applied along the direction of the two jumps orthogonal to 507 the line direction, represented in green in Fig. 8-(b). The jump direction is along 508 **b**, and it can be seen in Fig. 2 that indeed, this direction is located in the strip 509 of high absorption rates. It is actually the direction of highest absorption rate 510 in the plane (l, b) ($\varphi = 0^{\circ}$). From Fig. 2 it appears that maximum absorption 511 rates are obtained in a plane (l, n) ($\varphi = 90^{\circ}$). For a stress applied in this plane, 512 the projection of s on the jumps represented in red in Fig. 8-(b) is the highest 513 for $\theta = 71^{\circ}$; these four jumps are not orthogonal to the dislocation, but their 514 projection on l is small. The fact that four jumps contribute to SIA diffusion 515 enhancement in this case explains why the absorption rate is even higher than 516 for s along b. The value of θ found is very close to OKMC and CDM results 517 $(\theta = 76^{\circ}, \text{ Fig. 3})$ and B&R results $(\theta = 76^{\circ})$. The variation of θ from 90° 518 to 71° as φ varies from 0° to 90° explains the tilted strip in Fig. 2. Finally, 519 we note that in this discussion, the strain field of the dislocation has not been 520 considered. This validates the assumption of Woo to neglect the dislocation 521 field in the analytical treatment [16]. Fully considering lattice effects as in B&R 522 model appears necessary to obtain a good agreement with OKMC and CDM. We 523 note that although second order terms in Eq. (4) (fifth term and second part of 524 seventh term) can in principle also contribute to SIPA-AD, they certainly have 525 a very small impact as they are included in OKMC and CDM but not in B&R 526 model. 527

Even though B&R model successfully reproduces lattice effects, the magnitude of ΔZ^{AD} is significantly different from our calculations for both defects. This is especially the case for the vacancy. In the direction of applied stress where the absorption efficiency is the highest, the discrepancy reaches a factor of around 3. For this direction, the effects of anisotropy of dipole tensor



Figure 8: Orientation of uniaxial stress s leading to maximum absorption of point defects by a dislocation of line direction $l = [\bar{1}2\bar{1}]/\sqrt{6}$ and Burgers vector $b = [\bar{1}01]/\sqrt{2}$ ($n = [111]/\sqrt{3}$), and associated jumps responsible for this high absorption rate. (a) Absorption of vacancies (b) Absorption of SIAs; here we give the orientation of stress if it is applied in the planes defined by (l, b) ($\varphi = 0^{\circ}$) and (l, n) ($\varphi = 90^{\circ}$). The maximum absorption rate is obtained in this latest case, with four jumps contributing significantly to the absorption of SIAs.

at saddle configuration are the highest. In the model developed by Borodin and Ryazanov, the deviatoric part of the dipole tensor is assumed to be small compared to the hydrostatic part. This is not true for the vacancy, so it is not surprising that the model cannot quantitatively reproduce the values of ΔZ^{AD} when the dipole anisotropy contributes significantly to the absorption efficiency.

538 4.3.2. SIPA-I

Contrary to SIPA-AD, the dislocation strain field is an essential ingredient 539 in SIPA-I. The fourth term in Eq. (4), which induces a coupling between the 540 applied field and the dislocation field, gives rise to preferential diffusion of point 541 defects to some dislocations. Usually, one considers that SIAs are the main 542 contributors to SIPA-I, due to their large polarizability [75, 76, 38, 14, 77]. 543 HSW model (Eqs. (7)-(10)) predicts that SIAs will be absorbed preferentially by 544 dislocations whose Burgers vector is aligned with the applied stress [22, 23, 38]. 545 Our DFT calculations confirm that SIAs are much more polarizable than 546

vacancies (Tab. 1). Shear polarizabilities of SIAs and vacancies at stable point, 547 which are used in the analytical model, are found to differ by around one order 548 of magnitude. However, the effect of vacancies on SIPA-I is not completely neg-549 ligible (Fig. 5): the amplitude of the effect is only three times smaller than for 550 SIAs. This is essentially due to the high absorption efficiency of vacancies when 551 the stress is applied in the plane (l, n), for $\theta = 25^{\circ}$, close to the direction corre-552 sponding to a maximum of absorption efficiency for SIPA-AD ($\theta = 33^{\circ}$). This 553 behavior is not captured by HSW model. Additional calculations (not shown) 554 performed with CDM and using isotropic and identical properties at stable and 555 saddle points led to results in close agreement with HSW model. We can con-556 clude that this model is accurate in its framework and that the discrepancy 557 observed here is certainly due to lattice effects. On the contrary, the agreement 558 between the model and CDM is rather satisfactory for SIAs, although some 559 discrepancies appear if the stress is not normal to the dislocation line. This 560 shows that in general, since polarizabilities induce second order contributions, 561 they should not be considered without taking into account the first order con-562 tributions, *i.e.* of dipole anisotropy. To our knowledge, our simulations are 563 the first estimations of SIPA-I based on full account of first order terms and 564 polarizabilities at saddle configurations. 565

As for SIPA-AD, other terms potentially contributing to SIPA are included in CDM but not in the model. The first part of the seventh term in Eq. (4) leads to anisotropic diffusion, so to SIPA. However, for applied strains of the order of 10^{-4} as those considered here, this term can be safely neglected.

4.3.3. Relative contributions of SIPA-AD and SIPA-I to dislocation climb under stress

From analytical expressions as (6) and (11), it has been suggested that SIPA-AD is up to thirty times larger than SIPA-I [14, 12, 16]. It is interesting to see whether the present calculations, with more accurate values of dipole tensors and polarizabilities, confirm this conclusion. Indeed, considering polarizabilities induces additional complexity in kinetic codes, so it is useful to assess the rel-

evance of including them. From Figs. 2 and 5, one sees that the amplitude of 577 absorption efficiencies considering intrinsic dipole anisotropy only (SIPA-AD) is 578 around five times larger than the one due to polarizability (SIPA-I), whatever 579 the defect. However, as shown in Fig. 9, for a stress applied in a plane normal 580 to the dislocation line, polarizability reverses the directions of favored absorp-581 tion of SIAs. The reason for this is the low effect of dipole anisotropy in this 582 plane, at variance with polarizability. This suggests that polarizabilities cannot 583 be disregarded for studies under stress. 584

Including intrinsic dipole anisotropy and polarizability in the calculations 585 permits to conclude about the directions of applied stress which favor SIA or 586 vacancy absorption. From the present results it can be concluded that if the 587 stress is approximately orthogonal to the dislocation line, and in particular along 588 the Burgers vector, the net absorption rate of SIAs should be the highest. On 589 the contrary, a uniaxial stress applied close the $\langle 100 \rangle$ direction with the largest 590 projection on the dislocation line should minimize the net absorption rate of 591 SIAs. Since climb velocity under irradiation is generally driven by an excess of 592 absorbed SIAs due to EID, the climb velocity is expected to increase in the first 593 configuration and to decrease in the second one. 594

595 5. Conclusion

In this study we have investigated the effect of an applied uniaxial stress on 596 point defect absorption by straight dislocations in aluminum. Elastic dipoles and 597 diaelastic polarizabilities of vacancies and SIAs have been calculated by DFT at 598 stable and saddle points. These parameters have been used in an OKMC code 599 and a CDM model to evaluate absorption efficiencies under stress. Our results 600 confirm that the amplitude of SIPA-I, due to polarizability, is lower than the 601 one of SIPA-AD, due to dipole anisotropy, by a factor of around five. However, 602 the correct behavior of the absorption efficiency in a plane orthogonal to the 603 dislocation line can only be obtained if polarizability is considered, so neglecting 604 polarizability in studies under stress may not be appropriate. 605



Figure 9: Difference of absorption efficiency of SIAs ΔZ_i as a function of φ , calculated with CDM for $\theta = 90^{\circ}$. The reference calculation which is subtracted corresponds to a hydrostatic stress with only P_{ij} taken into account. The dashed curve shows the evolution of ΔZ_i if only P_{ij} is taken into account and the solid curve corresponds to the case where P_{ij} and α_{ijkl} are considered.

Simulation results have been compared to analytical expressions of SIPA-606 AD and SIPA-I. For SIAs, models are shown to be in reasonable agreement 607 with simulations. Vacancies are very anisotropic in their saddle configuration, 608 which induces strong lattice effects on the diffusion under stress. In this case 609 the predictions of the models are not very accurate. The expression of Borodin 610 and Ryazanov (B&R) for SIPA-AD includes lattice effects but it is assumed 611 that defects are weakly anisotropic in their saddle configuration. It correctly 612 predicts a maximum absorption rate of vacancies if the stress is applied along 613 the (100) direction with the largest projection on the dislocation line. However, 614 the amplitude of SIPA-AD is underestimated by a factor 3. The expression 615 for SIPA-I given by Woo (HSW model) relies on a simple isotropic description 616 of defects and is unable to reproduce the angular dependence of absorption 617

618 efficiency, which is similar to that of SIPA-AD.

Our results show that dislocation climb velocity under irradiation is expected 619 to be the highest if the stress is approximately orthogonal to the dislocation 620 line, especially along the Burgers vector, and the lowest if the stress is applied 621 close to the $\langle 100 \rangle$ direction with the largest projection on the dislocation line. 622 The dependence of these results on the symmetries of point defects in their 623 saddle configuration makes these conclusions likely transferable to other fcc 624 metals. The methodology used in this work can be applied to Frank dislocation 625 loops. It would be interesting to compare the obtained results to experimental 626 measurements of loop growth rates under stress [7], to better assess irradiation 627 creep mechanisms. 628

⁶²⁹ Appendix A. Modelling point defects as inhomogeneous inclusions

SIPA-I expressions (6)-(10) are more often given with notations related to 630 Eshelby inhomogenous inclusions. In this framework, a defect is considered as 63 a spherical inhomogeneity of bulk and shear moduli K^* and μ^* , respectively, 632 with a misfit corresponding to the transformation strain e_{ij}^* . It is convenient to 633 consider an equivalent homogeneous inclusion of transformation strain e_{ij}^{T} , which 634 depends on e_{ij}^* and on the local external strain field (sum of the dislocation and 635 applied strain fields), as well as on the elastic moduli of the inclusion and of the 636 matrix [78]. The elastic dipole is related to the equivalent transformation strain 637 through [29] 638

$$P_{ij} = \Omega C_{ijkl} e_{kl}^{\mathrm{T}},\tag{A.1}$$

639 with

$$C_{ijkl} = \left(K - \frac{2}{3}\mu\right)\delta_{ij}\delta_{kl} + \mu\left(\delta_{ik}\delta_{jl} + \delta_{il}\delta_{jk}\right).$$
(A.2)

In SIPA-I models, the defect is considered as isotropic, so $e_{kl}^{\rm T} = \delta_{kl} e^{\rm T}/3$. We obtain

$$P_{ij} = \Omega K e^{\mathrm{T}} \delta_{ij} = P \delta_{ij}, \qquad (A.3)$$

where P is the quantity used in Eqs. (6)-(10). It is customary to use the strain

within the inclusion in the absence of external field, e_{ij}^0 , related to e_{ij}^T by [78]

$$e_{ij}^0 = \mathcal{S}_{ijkl} e_{kl}^{\mathrm{T}},\tag{A.4}$$

⁶⁴⁴ where S_{ijkl} is the Eshelby tensor for a spherical inclusion:

$$S_{ijkl} = \frac{5\nu - 1}{15(1 - \nu)} \delta_{ij} \delta_{kl} + \frac{4 - 5\nu}{15(1 - \nu)} \left(\delta_{ik} \delta_{jl} + \delta_{il} \delta_{jk} \right).$$
(A.5)

The strain within the inclusion can be written as $e_{kl}^0 = \delta_{kl} e^0/3$, with

$$e^{0} = \frac{1+\nu}{3(1-\nu)}e^{\mathrm{T}} = \frac{1+\nu}{3(1-\nu)}\frac{P}{\Omega K}.$$
 (A.6)

We note that owing to Eqs. (17) and (A.3), e^{T} is the normalized relaxation volume in a finite medium $\Delta V^{\mathrm{r}}/\Omega$, whereas e^{0} is the normalized relaxation volume in an infinite medium $\Delta V^{\infty}/\Omega$, the deformation being localized at the position of the point defect [79].

By comparing the expressions of the interaction energy given by Eshelby [78] and the one obtained from Eqs. (2) and (5), the following expressions are obtained:

$$\alpha^{K} = -K\Omega \frac{3(1-\nu)\Delta K}{3(1-\nu)K + (1+\nu)\Delta K}$$
(A.7)

$$\alpha^{\mu} = -\mu \Omega \frac{15(1-\nu)\Delta\mu}{15(1-\nu)\mu + 2(4-5\nu)\Delta\mu},$$
(A.8)

653 with $\Delta K = K^* - K$ and $\Delta \mu = \mu^* - \mu$.

Appendix B. Set of deformation types to calculate polarizability ten sors

The structure of the polarizability tensors of vacancies and SIAs in their stable and saddle configurations depend on their symmetries. They are given in Table B.2. To determine all coefficients, we consider several deformation types (Tab. B.3). Since both initial ([100]) and final ([010]) configurations must be relaxed under applied strain in order to calculate the saddle position, the results

		Stab	ole cor	nfigura	ation			Sade	lle cor	nfigura	ation	
		Cu	ıbic sy	vmmet	try		(Orthor	homb	ic syn	nmetr	у
Vacancy								For [1	00] to	[010]	jump	
	$\left(\alpha_{11} \right)$	α_{12}	α_{12}	0	0	0)	$\left(\alpha_{11} \right)$	α_{12}	α_{13}	0	0	α_{16}
	α_{12}	α_{11}	α_{12}	0	0	0	α_{12}	α_{11}	α_{13}	0	0	α_{16}
	α_{12}	α_{12}	α_{11}	0	0	0	α_{13}	α_{13}	α_{33}	0	0	α_{36}
	0	0	0	α_{44}	0	0	0	0	0	α_{44}	α_{45}	0
	0	0	0	0	α_{44}	0	0	0	0	α_{45}	α_{44}	0
	0	0	0	0	0	α_{44}	α_{16}	α_{16}	α_{36}	0	0	α_{66}
		Tetra	agonal	symr	netry		(Orthor	homb	ic syn	nmetr	y
SIA		For [1	.00] co	onfigu	ration			For [1	00] to	[010]	jump	
	$\left(\alpha_{11} \right)$	α_{12}	α_{12}	0	0	0)	$\left(\alpha_{11} \right)$	α_{12}	α_{13}	0	0	α_{16}
	α_{12}	α_{22}	α_{23}	0	0	0	α_{12}	α_{11}	α_{13}	0	0	α_{16}
	α_{12}	α_{23}	α_{22}	0	0	0	α_{13}	α_{13}	α_{33}	0	0	α_{36}
	0	0	0	α_{44}	0	0	0	0	0	α_{44}	α_{45}	0
	0	0	0	0	α_{55}	0	0	0	0	α_{45}	α_{44}	0
	0	0	0	0	0	α_{55}	α_{16}	α_{16}	α_{36}	0	0	α_{66}

Table B.2: Structure of polarizability tensors of vacancies and SIAs in their stable and saddle configurations.

strain matrix	cubi	c symmetry	tetragonal s	symmetry	orthorhombic	: symmetry
	$-\frac{1}{2}\alpha_{ijkl}\varepsilon_{ij}\varepsilon_{kl}$	$-V\Delta\sigma_{ij} = \alpha_{ijkl}\varepsilon_{kl}$	$-rac{1}{2}lpha_{ijkl}arepsilon_{ij}arepsilon_{kl}$	$-V\Delta\sigma_{ij} = \alpha_{ijkl}\varepsilon_{kl}$	$-rac{1}{2}lpha_{ijkl}arepsilon_{ij}arepsilon_{kl}$	$-V\Delta\sigma_{ij} = \alpha_{ijkl}\varepsilon_{kl}$
$\mathbf{\hat{z}}_{1} = \begin{pmatrix} \varepsilon & 0 & 0 \\ 0 & \varepsilon & 0 \\ 0 & 0 & \varepsilon \end{pmatrix}$	$-\frac{3}{2}\left(\alpha_{11}+2\alpha_{12}\right)\varepsilon^{2}$	$-V\Delta\sigma_{11} = (\alpha_{11} + 2\alpha_{12})\varepsilon$	$-\tfrac{1}{2}(\alpha_{11}+2\alpha_{22}+4\alpha_{12}+2\alpha_{23})\varepsilon^2$	$-V\Delta\sigma_{11} = (\alpha_{11} + 2\alpha_{12})\varepsilon$ $-V\Delta\sigma_{22} = (\alpha_{12} + \alpha_{22} + \alpha_{23})\varepsilon$	$-\tfrac{1}{2}(2\alpha_{11}+2\alpha_{12}+\alpha_{33}+4\alpha_{13})\varepsilon^2$	$\begin{split} -V\Delta\sigma_{11} &= (\alpha_{11}+\alpha_{12}+\alpha_{13})\varepsilon\\ -V\Delta\sigma_{33} &= (2\alpha_{13}+\alpha_{33})\varepsilon\\ -V\Delta\sigma_{12} &= (2\alpha_{16}+\alpha_{36})\varepsilon \end{split}$
$^{2}=\begin{pmatrix}\varepsilon&0&0\\0&0&0\\0&0&0\end{pmatrix}$	$-\frac{1}{2}\Delta_{11}c^2$	$-V\Delta\sigma_{11} = \alpha_{11}\varepsilon$ $-V\Delta\sigma_{22} = \alpha_{12}\varepsilon$	$-\frac{1}{2}\alpha_{11}\varepsilon^2 \\ -\frac{1}{2}\alpha_{22}\varepsilon^2(\omega)$	$-V\Delta\sigma_{11} = \alpha_{11}\varepsilon$ $-V\Delta\sigma_{22} = \alpha_{12}\varepsilon$ $-V\Delta\sigma_{11} = \alpha_{22}\varepsilon^{(n)}$ $-V\Delta\sigma_{22} = \alpha_{12}\varepsilon^{(n)}$ $-V\Delta\sigma_{33} = \alpha_{23}\varepsilon^{(n)}$	- <u>1</u> 011 c ²	$-V\Delta\sigma_{11} = \alpha_{11}\varepsilon$ $-V\Delta\sigma_{22} = \alpha_{12}\varepsilon$ $-V\Delta\sigma_{33} = \alpha_{13}\varepsilon$ $-V\Delta\sigma_{12} = \alpha_{16}\varepsilon$
$\varepsilon_3 = \begin{pmatrix} 0 & 0 & 0 \\ 0 & 0 & \varepsilon \\ 0 & \varepsilon & 0 \end{pmatrix}$	$-2a_{44}\epsilon^2$	$-V\Delta\sigma_{23} = 2lpha_{44}\varepsilon$	$-2a_{44}\varepsilon^2$ $-2a_{55}\varepsilon^{2(a)}$	$-V\Delta\sigma_{23} = 2\alpha_{44}\varepsilon$ $-V\Delta\sigma_{23} = 2\alpha_{55}\varepsilon^{(a)}$	$-2a_{44}\varepsilon^2$	$-V\Delta\sigma_{23} = 2\alpha_{44}\varepsilon$ $-V\Delta\sigma_{13} = 2\alpha_{45}\varepsilon$
$\mathbf{c}_4 = \begin{pmatrix} 0 & \varepsilon & 0 \\ \varepsilon & 0 & 0 \\ 0 & 0 & 0 \end{pmatrix}$	Equi	valent to $\boldsymbol{\varepsilon}_3$	Equivalent to ε_3 on	final configuration	$-2\alpha_{66}\varepsilon^2$	$-V\Delta\sigma_{11} = 2\alpha_{16}\varepsilon$ $-V\Delta\sigma_{33} = 2\alpha_{36}\varepsilon$ $-V\Delta\sigma_{33} = 2\alpha_{66}\varepsilon$

for the SIA and [100] to [010] ii Table R 2 ([100] 2 olarizahilit al and orthorhombio tet ahility inalo 4 d din. d related v Table B.3: Stra respectively), ur

(a) On final configuration (SIA oriented along [010])

concerning the final configurations can also be exploited to obtain additional
 data about coefficients of the polarizability tensor.

Figures B.10 and B.11 show the variation of energy due to polarizability, called $E^{(2)}$ (see Tab. B.3) extracted from DFT simulations (solid lines) and calculated with the elastic model using polarizabilities deduced from residual stress (in dashed lines). The variation of residual stress due to polarizability, $-V\Delta\sigma_{ij} = \alpha_{ijkl}\varepsilon_{kl}$, is also shown. These two deformations (1 and 3, see Tab. B.3) correspond to dilatation/compression and $\langle 100 \rangle$ shear.



Figure B.10: Deformation 1 (dilatation/compression): (a) Variation of energy due to polarizability, extracted from DFT simulations (symbols with fit in solid lines) and calculated with the elastic model using polarizabilities extracted from residual stress (dashed lines). (b) Variation of residual stress (*i. e.* change in dipole tensors) due to polarizability, which is fitted with a linear function to extract polarizabilities.

669 Acknowledgments

T. J. acknowledges F. Willaime for discussions about DFT calculations and Y. Le Bouar for discussions about polarizabilities. This work was performed using HPC resources from GENCI-CINES (Grant 2020-A0100912414).



Figure B.11: Deformation 3 ($\langle 100 \rangle$ shear): (a) Variation of energy due to polarizability, extracted from DFT simulations (symbols with fit in solid lines) and calculated with the elastic model using polarizabilities extracted from residual stress (dashed lines). (b) Variation of residual stress (*i. e.* change in dipole tensors) due to polarizability, which is fitted with a linear function to extract polarizabilities.

673 Data availability

The relevant data are available within the article or from the authors upon reasonable request.

676 References

- [1] J. R. Matthews, M. W. Finnis, Irradiation creep models An overview, J.
 Nucl. Mater. 159 (1988) 257.
- ⁶⁷⁹ [2] F. Onimus, T. Jourdan, C. Xu, A. A. Campbell, M. Griffiths, 1.10 irradiation creep in materials, in: Comprehensive Nuclear Materials, Elsevier,
 ⁶⁸¹ 2020, p. 310.
- [3] P. R. Okamoto, S. D. Harkness, Stress-biased loop nucleation in irradiated
 type 316 stainless steels, J. Nucl. Mater. 48 (1973) 204.
- [4] F. A. Garner, W. G. Wolfer, H. R. Brager, A reassessment of the role
 of stress in development of radiation-induced microstructure, in: J. A.
 Sprague, D. Kramer (Eds.), Effects of radiation on structural materials,
 ASTM STP 683, 1979, p. 160.
- [5] D. Faulkner, R. J. McElroy, Irradiation creep and growth in zirconium
 during proton bombardment, in: J. A. Sprague, D. Kramer (Eds.), Effects
 of Radiation on Structural Materials: ASTM STP 683, 1979, p. 329.
- [6] F. A. Garner, D. S. Gelles, Irradiation creep mechanisms: an experimental
 perspective, J. Nucl. Mater. 159 (1988) 286.
- [7] S. Jitsukawa, Y. Katano, K. Shiraishi, F. A. Garner, The Behavior of
 Irradiation-Produced Dislocation Loops under External Stress during Elec tron Irradiation, in: R. E. Stoller, A. S. Kumar, D. S. Gelles (Eds.), Effects
- of Radiation on Materials: 15th International Symposium, 1992, p. 1034.
- [8] C. Xu, G. S. Was, Anisotropic dislocation loop distribution in alloy T91
 during irradiation creep, J. Nucl. Mater. 454 (2014) 255.

- ⁶⁹⁹ [9] W. G. Wolfer, Correlation of radiation creep theory with experimental ev ⁷⁰⁰ idence, J. Nucl. Mater. 90 (1980) 175.
- [10] W. G. Wolfer, L. K. Mansur, J. A. Sprague, Theory of swelling and irradiation creep, in: M. L. Bleiberg, J. W. Bennett (Eds.), Radiation Effects in
 Breeder Reactor Structural Materials, 1977, p. 479.
- [11] L. K. Mansur, Irradiation creep by climb-enabled glide of dislocations resulting from preferred absorption of point defects, Philos. Mag. A 39 (1979)
 497.
- [12] C. H. Woo, E. J. Savino, Stress-induced preferred absorption due to saddle point anisotropy: the case of an infinitesimal dislocation loop, J. Nucl.
 Mater. 116 (1983) 17.
- [13] B. C. Skinner, C. H. Woo, Shape effect in the drift diffusion of point defects
 into straight dislocations, Phys. Rev. B 30 (1984) 3084.
- [14] E. J. Savino, C. N. Tomé, Irradiation creep by stress-induced preferential
 attraction due to anisotropic diffusion (SIPA-AD), J. Nucl. Mater. 108 &
 109 (1982) 405.
- [15] C. N. Tomé, H. A. Cecatto, E. J. Savino, Point-defect diffusion in a strained
 crystal, Phys. Rev. B 25 (1982) 7428.
- [16] C. H. Woo, Irradiation creep due to elastodiffusion, J. Nucl. Mater. 120
 (1984) 55.
- [17] V. A. Borodin, A. I. Ryazanov, The effect of diffusion anisotropy on dislocation bias and irradiation creep in cubic lattice materials, J. Nucl. Mater.
 210 (1994) 258.
- [18] H. R. Schober, Single and multiple interstitials in FCC metals, J. Phys. F:
 Metal Phys. 7 (1977) 1127.
- [19] E. J. Savino, Point defect-dislocation interaction in a crystal under tension,
 Philos. Mag. 36 (1977) 323.

- [20] P. H. Dederichs, K. Schroeder, Anisotropic diffusion in stress fields, Phys.
 Rev. B 17 (1978) 2524.
- [21] P. T. Heald, M. V. Speight, Steady-state irradiation creep, Philos. Mag. 29
 (1974) 1075.
- [22] R. Bullough, J. R. Willis, The stress-induced point defect-dislocation in teraction and its relevance to irradiation creep, Philos. Mag. 31 (1975) 855.
- [23] P. T. Heald, M. V. Speight, Point defect behaviour in irradiated materials,
 Acta Metall. 23 (1975) 1389.
- [24] W. Schilling, Self-interstitial atoms in metals, J. Nucl. Mater. 69 & 70
 (1978) 465.
- [25] C. Varvenne, E. Clouet, Elastic dipoles of point defects from atomistic
 simulations, Phys. Rev. B 96 (2017) 224103.
- [26] D. Carpentier, T. Jourdan, Y. Le Bouar, M.-C. Marinica, Effect of saddle
 point anisotropy of point defects on their absorption by dislocations and
 cavities, Acta Mater. 136 (2017) 323.
- [27] T. Jourdan, A. Vattré, A continuous model including elastodiffusion for
 sink strength calculation of interfaces, Comput. Mater. Sci. 153 (2018) 473.
- [28] R. Siems, Mechanical interactions of point defects, Phys. Stat. Sol. 30
 (1968) 645.
- [29] E. Clouet, C. Varvenne, T. Jourdan, Elastic modeling of point-defects and
 their interactions, Comp. Mater. Sci. 147 (2018) 49.
- [30] H. R. Schober, Polarizabilities of point defects in metals, J. Nucl. Mater.
 126 (1984) 220.
- [31] A. D. Brailsford, R. Bullough, The rate theory of swelling due to void
 growth in irradiated metals, J. Nucl. Mater. 44 (1972) 121.

- [32] A. D. Brailsford, R. Bullough, M. R. Hayns, Point defect sink strengths
 and void-swelling, J. Nucl. Mater. 60 (1976) 246–256.
- [33] F. A. Nichols, On the estimation of sink-absorption terms in reaction-ratetheory analysis of radiation damage, J. Nucl. Mater. 75 (1978) 32.
- [34] C. H. Woo, The sink strength of a dislocation loop in the effective medium
 approximation, J. Nucl. Mater. 98 (1981) 279.
- ⁷⁵⁷ [35] T. Jourdan, Influence of dislocation and dislocation loop biases on mi⁷⁵⁸ crostructures simulated by rate equation cluster dynamics, J. Nucl. Mater.
 ⁷⁵⁹ 467 (2015) 286.
- [36] A. A. Kohnert, L. Capolungo, Sink strength and dislocation bias of three dimensional microstructures, Phys. Rev. Mater. 3 (2019) 053608.
- [37] W. G. Wolfer, M. Ashkin, Diffusion of vacancies and interstitials to edge
 dislocations, J. Appl. Phys. 47 (1976) 791.
- ⁷⁶⁴ [38] C. H. Woo, Effects of an anisotropic dislocation structure on irradiation
 ⁷⁶⁵ creep due to stress induced preferred absorption of point defects, J. Nucl.
 ⁷⁶⁶ Mater. 80 (1979) 132.
- ⁷⁶⁷ [39] P. Ehrhart, P. Jung, H. Schultz, H. Ullmaier, Landolt–Börnstein, Numeri⁷⁶⁸ cal Data and Functional Relationships in Science and Technology, Atomic
 ⁷⁶⁹ Defects In Metals, Springer, 1991.
- [40] I.-W. Chen, Anisotropic diffusion of point defects to edge dislocations, J.
 Nucl. Mater. 125 (1984) 52.
- [41] G. F. Bouobda Moladje, L. Thuinet, C. Domain, C. S. Becquart, A. Legris,
 Phase-field calculations of sink strength in Al, Ni, and Fe: A detailed study
 of elastic effects, Comput. Mater. Sci. 183 (2020) 109905.
- [42] V. A. Borodin, The effect of swelling on SIPA irradiation creep, J. Nucl.
 Mater. 225 (1995) 15.

- [43] A. Vattré, T. Jourdan, H. Ding, M.-C. Marinica, M. J. Demkowicz, Non-777 random walk diffusion enhances the sink strength of semicoherent inter-778 faces, Nat. Commun. 7 (2016) 10424. 779
- [44] E. Clouet, A. Bakaev, V. Borodin, Z. Chang, C. C. Fu, M. C. Marinica, 780 P. Olsson, M. Posselt, D. Terentyev, P. Vladimirov, E. E. Zhurkin, Screen-781 ing of irradiation creep mechanisms using atomic-level simulation tools, 782 Tech. rep., MATISSE project (2017).
- URL http://fp7-matisse.eu/public-project-reports/ 784

783

- [45] E. Clouet, S. Garruchet, H. Nguyen, M. Perez, C. S. Becquart, Dislocation 785 interaction with C in α -Fe: A comparison between atomic simulations and 786 elastic theory, Acta Mater. 56 (2008) 3450. 787
- [46] G. Kresse, J. Hafner, *Ab initio* molecular dynamics for liquid metals, Phys. 788 Rev. B 47 (1993) 558. 78
- [47] G. Kresse, J. Hafner, Ab initio molecular-dynamics simulation of the liquid-790 metal-amorphous-semiconductor transition in germanium, Phys. Rev. B 49 791 (1994) 14251. 792
- [48] G. Kresse, J. Furthmüller, Efficiency of ab-initio total energy calcula-793 tions for metals and semiconductors using a plane-wave basis set, Comput. 79 Mater. Sci. 6 (1996) 15. 795
- [49] G. Kresse, J. Furthmüller, Efficient iterative schemes for *ab initio* total-796 energy calculations using a plane-wave basis set, Phys. Rev. B 54 (1996) 797 11169.798
- [50] P. E. Blöchl, Projector augmented-wave method, Phys. Rev. B 50 (1994) 799 17953. 800
- [51] G. Kresse, D. Joubert, From ultrasoft pseudopotentials to the projector 801 augmented-wave method, Phys. Rev. B 59 (1999) 1758. 802

- ⁸⁰³ [52] N. Chetty, M. Weinert, T. S. Rahman, J. W. Davenport, Vacancies and
 ⁸⁰⁴ impurities in aluminum and magnesium, Phys. Rev. B 52 (9) (1995) 6313.
- ⁸⁰⁵ [53] G. Henkelman, B. P. Uberuaga, H. Jónsson, A climbing image nudged
 ⁸⁰⁶ elastic band method for finding saddle points and minimum energy paths,
 ⁸⁰⁷ J. Chem. Phys. 113 (2000) 9901.
- [54] M. A. Caro, S. Schulz, E. P. O'Reilly, Comparison of stress and total energy
 methods for calculation of elastic properties of semiconductors, J. Phys.:
 Condens. Matter 25 (2013) 025803.
- ⁸¹¹ [55] D. Connétable, P. Maugis, Effect of stress on vacancy formation and diffu⁸¹² sion in fcc systems: Comparison between DFT calculations and elasticity
 ⁸¹³ theory, Acta Mater. 200 (2020) 869.
- ⁸¹⁴ [56] V. Spirić, L. E. Rehn, K.-H. Robrock, W. Schilling, Anelastic relaxation
 ⁸¹⁵ due to single self-interstitial atoms in electron-irradiated Al, Phys. Rev. B
 ⁸¹⁶ 15 (1977) 672.
- [57] K.-H. Robrock, W. Schilling, Diaelastic modulus change of aluminum after
 low temperature electron irradiation, J. Phys. F: Metal Phys. 6 (3) (1976)
 303.
- [58] P. H. Dederichs, C. Lehmann, A. Scholz, Change of elastic constants due
 to interstitials, Z. Physik B 20 (1975) 155.
- ⁸²² [59] J. Holder, A. V. Granato, L. E. Rehn, Effects of self-interstitials and close
 ⁸²³ pairs on the elastic constants of copper, Phys. Rev. B 10 (2) (1974) 363.
- [60] L. E. Rehn, J. Holder, A. V. Granato, R. R. Coltman, F. W. Young, Jr,
 Effects of thermal-neutron irradiation on the elastic constants of copper,
 Phys. Rev. B 10 (2) (1974) 349.
- ⁸²⁷ [61] M. P. Puls, C. H. Woo, Diaelastic polarizabilities due to vacancies and ⁸²⁸ interstitials in metals, J. Nucl. Mater. 139 (1986) 48.

- [62] G. J. Ackland, Theoretical study of the effect of point defects on the elastic
 constants of copper, J. Nucl. Mater. 152 (1988) 53.
- [63] H.-G. Haubold, Study of irradiation induced point defects by diffuse scattering, in: Proc. Int. Conf. Fundamental Aspects of Radiation Damage in
 Metals, 1975, p. 268.
- ⁸³⁴ [64] R. M. Emrick, P. B. McArdle, Effect of pressure on quenched-in electrical
 ⁸³⁵ resistance in gold and aluminum, Phys. Rev. 188 (1969) 1156.
- [65] P. Ehrhart, W. Schilling, Investigation of interstitials in electron-irradiated
 aluminum by diffuse-X-ray scattering experiments, Phys. Rev. B 8 (6)
 (1973) 2604.
- ⁸³⁹ [66] B. J. Buescher, R. M. Emrick, Pressure effect on defect migration in aluminum, Phys. Rev. B 1 (10) (1970) 3922.
- ⁸⁴¹ [67] R. C. Folweiler, F. R. Brotzen, The effect of quenched-in vacancies on the
 ⁸⁴² elastic modulus of aluminum, Acta Metall. 7 (1959) 716.
- [68] H. R. Brager, F. A. Garner, E. R. Gilbert, J. E. Flinn, W. G. Wolfer,
 Stress-affected microstructural development and the creep-swelling interrelationship, in: M. L. Bleiberg, J. W. Bennett (Eds.), Radiation Effects in
 Breeder Reactor Structural Materials, The Metallurgical Society of AIME,
 1977, p. 727.
- [69] W. P. Kuykendall, W. Cai, Conditional convergence in two-dimensional
 dislocation dynamics, Modelling Simul. Mater. Sci. Eng. 21 (2013) 055003.
- [70] D. T. Gillespie, A general method for numerically simulating the stochastic
 time evolution of coupled chemical reactions, J. Comput. Phys. 22 (1976)
 403.
- [71] A. B. Bortz, M. H. Kalos, J. L. Lebowitz, A New Algorithm for MonteCarlo Simulation of Ising Spin Systems, J. Comput. Phys. 17 (1975) 10.

- [72] B. Zhang, C. Wheatley, P. Chen, X. Qian, M. J. Demkowicz, Shear strain
 alters the structure and migration of self-interstitial atoms in copper, Phys.
 Rev. Mater. 6 (2022) 053605.
- ⁸⁵⁸ [73] H. Flyvbjerg, H. G. Petersen, Error estimates on averages of correlated
 ⁸⁵⁹ data, J. Chem. Phys. 91 (1989) 461.
- [74] C. H. Woo, Intrinsic bias differential between vacancy loops and interstitial
 loops, J. Nucl. Mater. 107 (1982) 20.
- ⁸⁶² [75] R. Bullough, M. R. Hayns, Irradiation-creep due to point defect absorption,
 J. Nucl. Mater. 57 (1975) 348.
- ⁸⁶⁴ [76] P. T. Heald, Radiation-induced creep and swelling, in: M. L. Bleiberg, J. W.
 ⁸⁶⁵ Bennett (Eds.), Radiation Effects in Breeder Reactor Structural Materials,
 ⁸⁶⁶ 1977, p. 781.
- ⁸⁶⁷ [77] C. Xu, G. S. Was, Proton irradiation creep of FM steel T91, J. Nucl. Mater.
 ⁸⁶⁸ 459 (2015) 183.
- ⁸⁶⁹ [78] J. D. Eshelby, The determination of the elastic field of an ellipsoidal inclu ⁸⁷⁰ sion, and related problems, Proceedings of the Royal Society of London.
- Series A. Mathematical and Physical Sciences 241 (1957) 376.
- [79] G. Leibfried, N. Breuer, Point Defects in Metals I, in: Springer Tracts in
 Modern Physics, Springer-Verlag, Berlin, 1978.